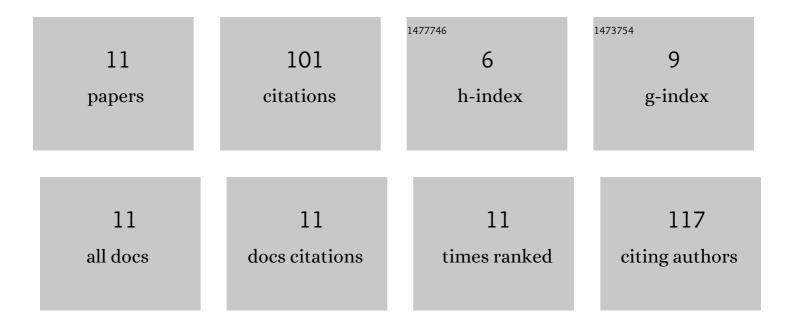
Jennifer L Taggart

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/3255023/publications.pdf Version: 2024-02-01



IENNIEED | TACCART

#	Article	IF	CITATIONS
1	Ionizing Radiation Effects on Nonvolatile Memory Properties of Programmable Metallization Cells. IEEE Transactions on Nuclear Science, 2014, 61, 2985-2990.	1.2	29
2	Radiation Hardening by Process of CBRAM Resistance Switching Cells. IEEE Transactions on Nuclear Science, 2016, 63, 2145-2151.	1.2	15
3	Evaluation of Radiation Effects in RRAM-Based Neuromorphic Computing System for Inference. IEEE Transactions on Nuclear Science, 2019, 66, 97-103.	1.2	14
4	Total-Ionizing-Dose Effects on Resistance Stability of Programmable Metallization Cell Based Memory and Selectors. IEEE Transactions on Nuclear Science, 2017, 64, 269-276.	1.2	11
5	Training a Neural Network on Analog TaO _{<italic>x</italic>} ReRAM Devices Irradiated With Heavy Ions: Effects on Classification Accuracy Demonstrated With CrossSim. IEEE Transactions on Nuclear Science, 2019, 66, 54-60.	1.2	8
6	Flexible Ag-ChG Radiation Sensors: Limit of Detection and Dynamic Range Optimization Through Physical Design Tuning. IEEE Transactions on Nuclear Science, 2016, 63, 2137-2144.	1.2	7
7	Effects of 14 MeV neutron irradiation on the DC characteristics of CBRAM cells. , 2016, , .		5
8	Resistance State Locking in CBRAM Cells Due to Displacement Damage Effects. IEEE Transactions on Nuclear Science, 2017, , 1-1.	1.2	5
9	<italic>In Situ</italic> Synaptic Programming of CBRAM in an Ionizing Radiation Environment. IEEE Transactions on Nuclear Science, 2018, 65, 192-199.	1.2	5
10	Failure Thresholds in CBRAM Due to Total Ionizing Dose and Displacement Damage Effects. IEEE Transactions on Nuclear Science, 2019, 66, 69-76.	1.2	2
11	A Comparative Study on TID Influenced Lateral Diffusion of Group 11 Metals into GexS _{1-x } and Ge _x Se _{1-x} Systems: A Flexible Radiation Sensor Development	1.2	0